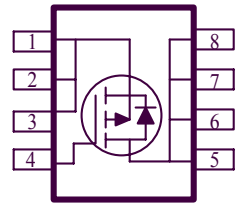
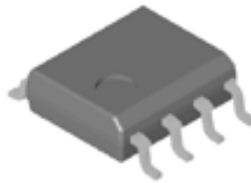


## P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low  $r_{DS(on)}$  Provides Higher Efficiency and Extends Battery Life
- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range ( $\pm 25$ ) for battery pack applications



PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ m( $\Omega$ )	$I_D$ (A)
-30	30 @ $V_{GS} = -10V$	9.5
	52 @ $V_{GS} = -4.5V$	7.5

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	$\pm 25$	
Continuous Drain Current <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	9.5	A
	$T_A = 70^\circ\text{C}$		8.3	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	$\pm 50$	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	-2.1	A
Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	3.1	W
	$T_A = 70^\circ\text{C}$		2.6	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Case <sup>a</sup>	$t \leq 5 \text{ sec}$	$R_{\theta JC}$	25	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	50	$^\circ\text{C/W}$

#### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

**SPECIFICATIONS ( $T_A = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 uA	-30			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 uA	-1	-1.6	-3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±25 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V			-1	uA
		V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C			-5	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -10 V	-50			A
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -9.5 A		24	30	mΩ
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -7.5 A		44	52	
		V <sub>GS</sub> = -10 V, I <sub>D</sub> = -9.5 A, T <sub>J</sub> = 55 <sup>0</sup> C		29	36	
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -9.5 A		31		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -2.1 A, V <sub>GS</sub> = 0 V		-0.7	-1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -9.5 A		15	26	nC
Gate-Source Charge	Q <sub>gs</sub>			5.8		
Gate-Drain Charge	Q <sub>gd</sub>			12		
Switching						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 15 Ω , I <sub>D</sub> = -1 A, V <sub>GEN</sub> = -10 V, R <sub>G</sub> = 6Ω		15	26	nS
Rise Time	t <sub>r</sub>			12	21	
Turn-Off Delay Time	t <sub>d(off)</sub>			62	108	
Fall-Time	t <sub>f</sub>			46	71	

## Notes

- Pulse test:  $PW \leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

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## Typical Electrical Characteristics (P-Channel)

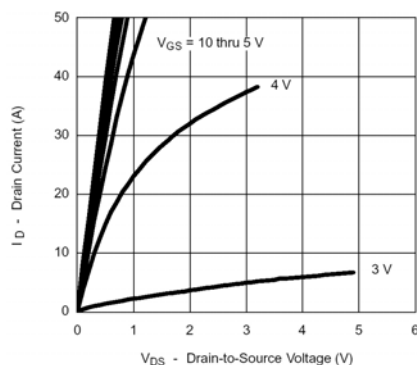


Figure 1. On-Region Characteristics

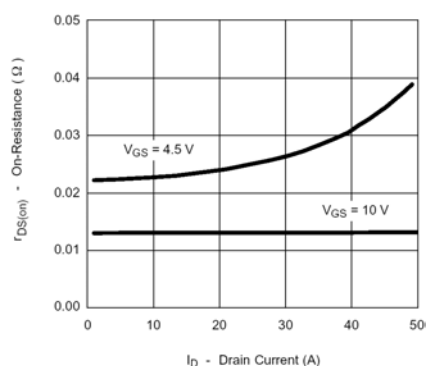


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

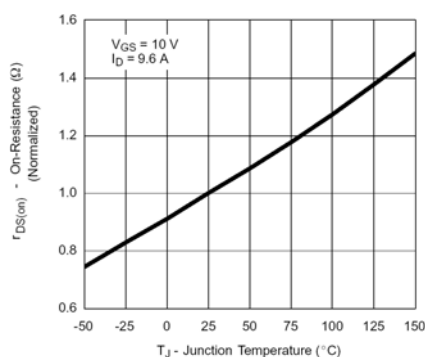


Figure 3. On-Resistance Variation with Temperature

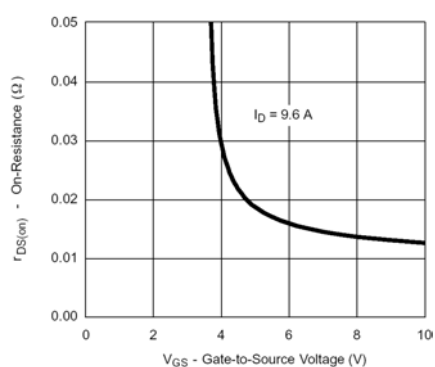


Figure 4. On-Resistance Variation with Gate to Source Voltage

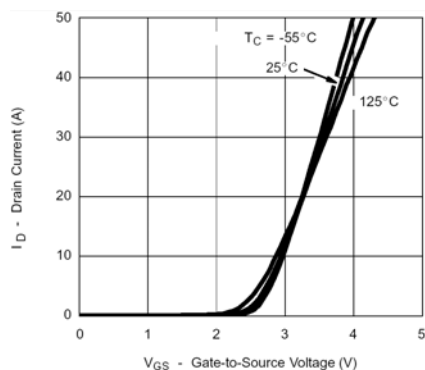


Figure 5. Transfer Characteristics

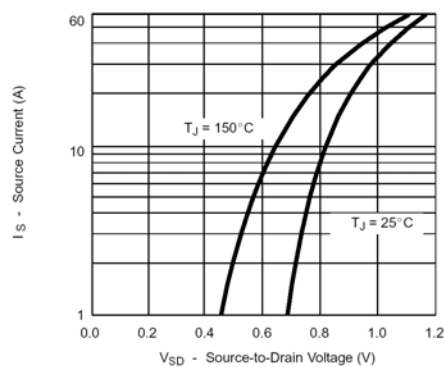


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

## Typical Electrical Characteristics (P-Channel)

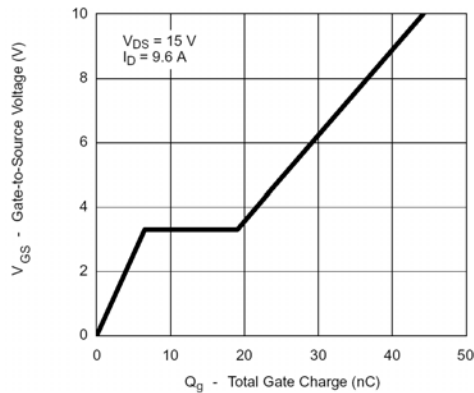


Figure 7. Gate Charge Characteristics

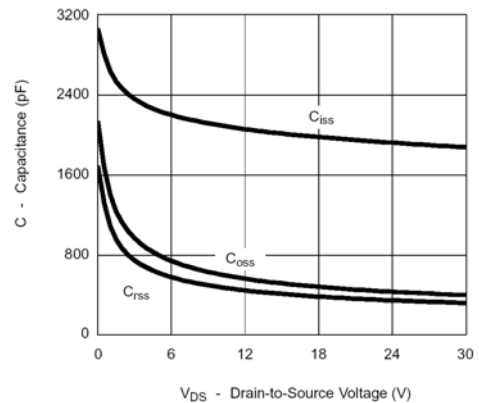


Figure 8. Capacitance Characteristics

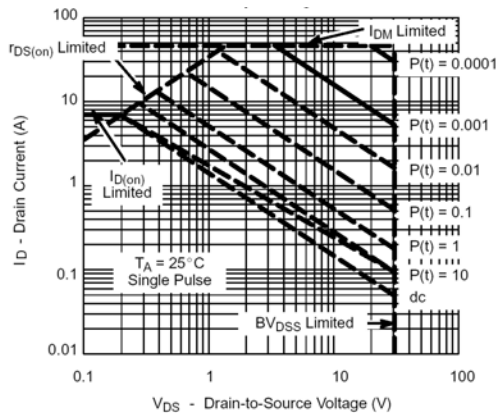


Figure 9. Maximum Safe Operating Area

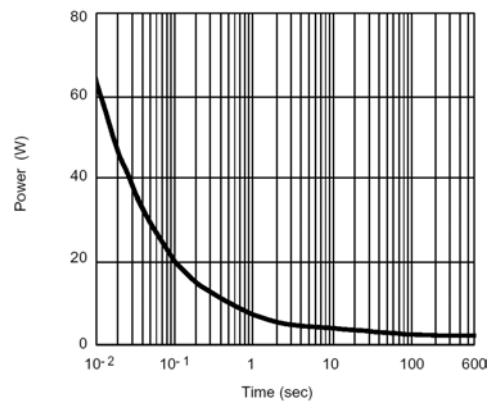


Figure 10. Single Pulse Maximum Power Dissipation

### Normalized Thermal Transient Junction to Ambient

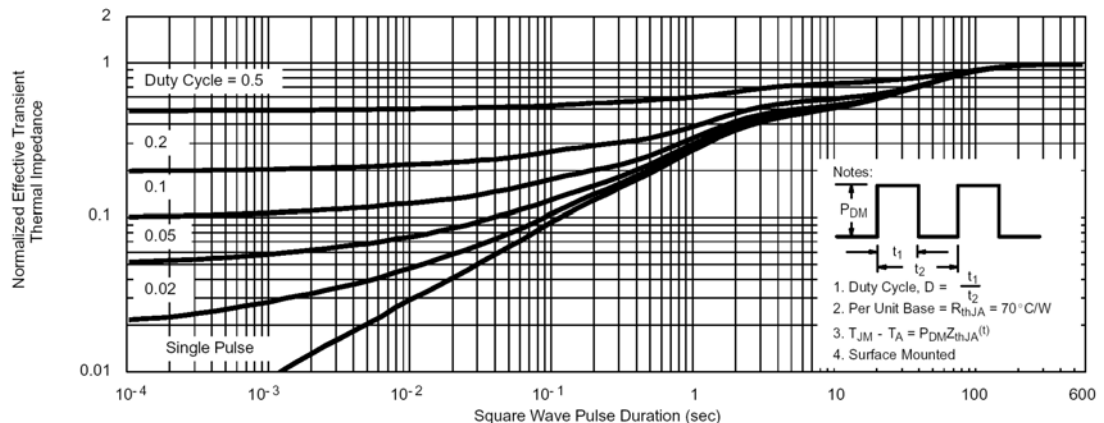
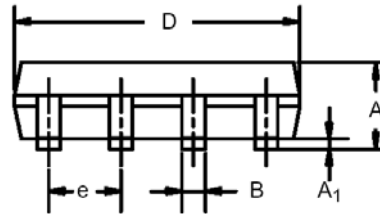
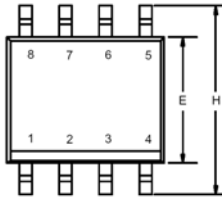


Figure 11. Transient Thermal Response Curve

## Package Information

## SO-8: 8LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

